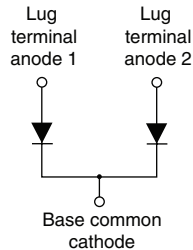


## HEXFRED® Ultrafast Soft Recovery Diode, 240 A



TO-244


**FEATURES**

- Very low  $Q_{rr}$  and  $t_{rr}$
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS  
COMPLIANT**
**BENEFITS**

- Reduced RFI and EMI
- Reduced snubbing

**DESCRIPTION**

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and  $di/dt$  simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

**PRODUCT SUMMARY**

$I_{F(AV)}$	240 A
$V_R$	400 V
$I_{F(DC)}$ at $T_C$	197 A at 100 °C

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	$V_R$		400	V
Continuous forward current	$I_F$	$T_C = 25\text{ °C}$	395	A
		$T_C = 100\text{ °C}$	197	
Single pulse forward current	$I_{FSM}$	Limited by junction temperature	900	
Non-repetitive avalanche energy	$E_{AS}$	$L = 100\ \mu\text{H}$ , duty cycle limited by maximum $T_J$	1.4	mJ
Maximum power dissipation	$P_D$	$T_C = 25\text{ °C}$	658	W
		$T_C = 100\text{ °C}$	263	
Operating junction and storage temperature range	$T_J, T_{Stg}$		- 55 to + 150	°C

**ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$  unless otherwise specified)**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	$V_{BR}$	$I_R = 100\ \mu\text{A}$	400	-	-	V	
Maximum forward voltage	$V_{FM}$	$I_F = 120\text{ A}$	-	1.1	1.47		
		$I_F = 240\text{ A}$	See fig. 1	-	1.3		1.5
		$I_F = 120\text{ A}, T_J = 125\text{ °C}$		-	1.0	1.2	
Maximum reverse leakage current	$I_{RM}$	$T_J = 125\text{ °C}, V_R = 400\text{ V}$	See fig. 2	-	660	5000	$\mu\text{A}$
Junction capacitance	$C_T$	$V_R = 200\text{ V}$	See fig. 3	-	280	380	pF
Series inductance	$L_S$	From top of terminal hole to mounting plane	-	6.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t <sub>rr</sub>	I <sub>F</sub> = 1.0 A, di <sub>F</sub> /dt = 200 A/μs, V <sub>R</sub> = 30 V	-	50	-	ns
		T <sub>J</sub> = 25 °C	-	77	120	
		T <sub>J</sub> = 125 °C	-	290	440	
Peak recovery current See fig. 6	I <sub>R</sub> RM	T <sub>J</sub> = 25 °C	-	7.5	14	A
		T <sub>J</sub> = 125 °C	-	16	30	
Reverse recovery charge See fig. 7	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	-	290	780	nC
		T <sub>J</sub> = 125 °C	-	2300	6300	
Peak rate of recovery current See fig. 8	di <sub>(rec)</sub> M/dt	T <sub>J</sub> = 25 °C	-	320	-	A/μs
		T <sub>J</sub> = 125 °C	-	270	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>	- 55	-	150	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>	per leg	-	-	0.19	°C/W
		per module	-	-	0.095	
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>	-	0.10	-		
Weight		-	68	-	g	
		-	2.4	-	oz.	
Mounting torque	(1)	30 (3.4)	-	40 (4.6)	N · m (lbf · in)	
	center hole	12 (1.4)	-	18 (2.1)		
Terminal torque		30 (3.4)	-	40 (4.6)		
Vertical pull		-	-	80	lbf · in	
2" lever pull		-	-	35		

**Note**

(1) Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film of thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached.

## HEXFRED® Ultrafast Soft Recovery Diode, 240 A

Vishay High Power Products

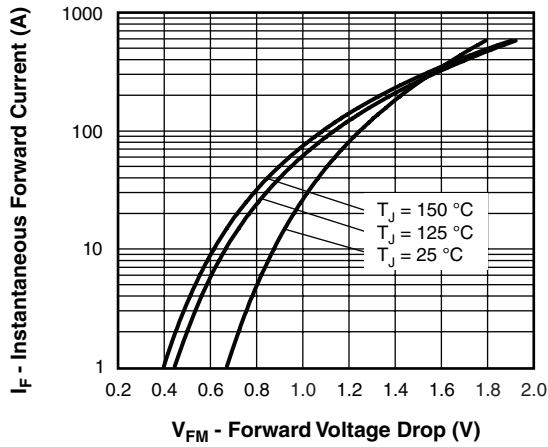


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

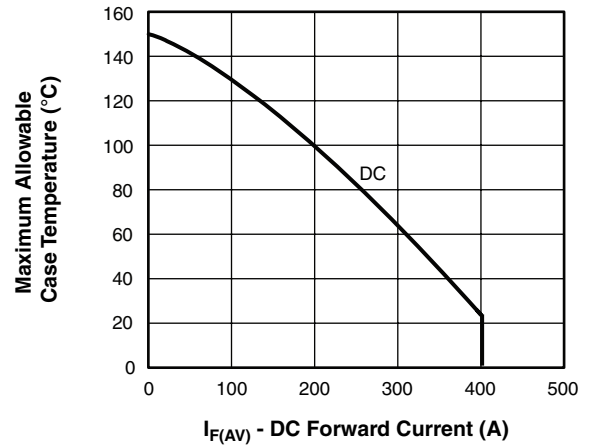


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current (Per Leg)

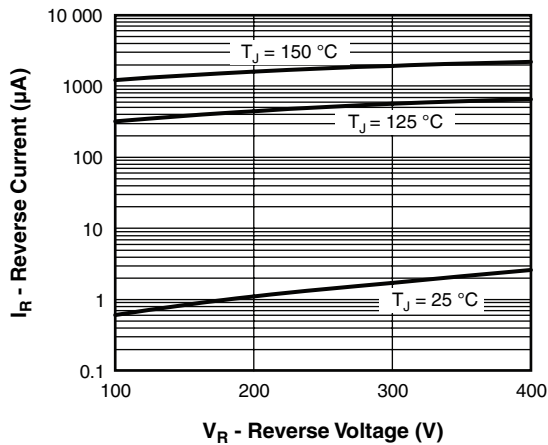


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

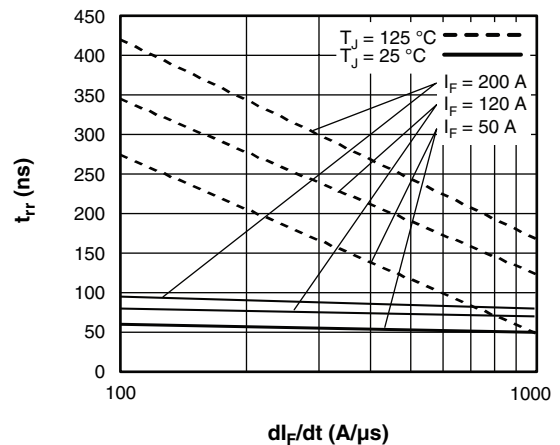


Fig. 5 - Typical Reverse Recovery Time vs.  $di_F/dt$  (Per Leg)

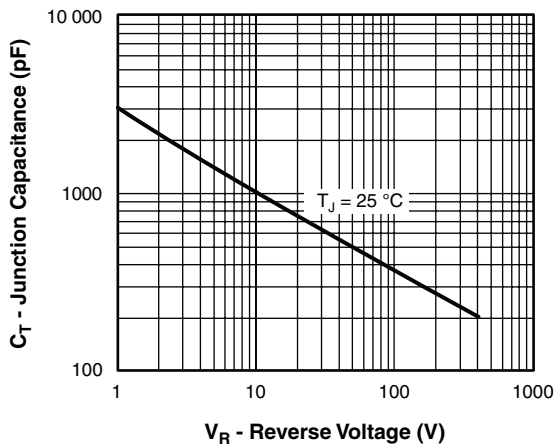


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

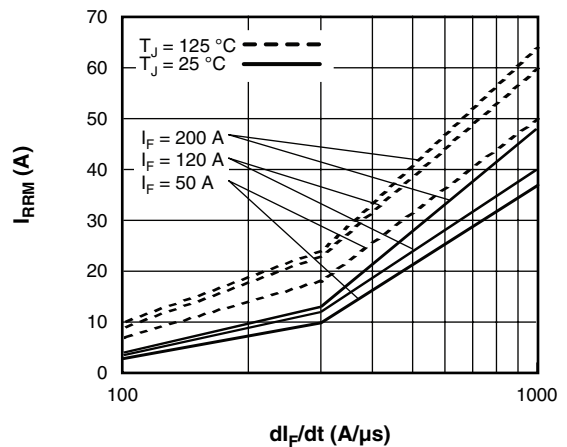


Fig. 6 - Typical Recovery Current vs.  $di_F/dt$  (Per Leg)

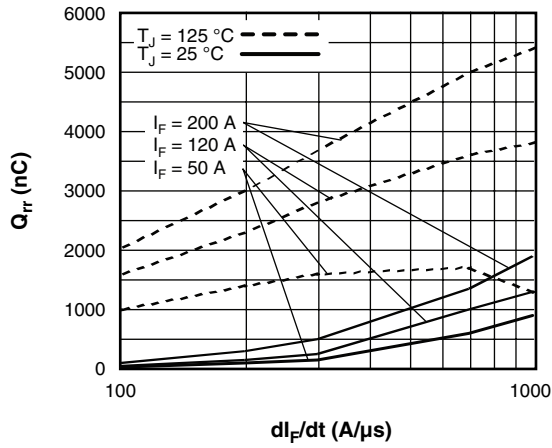


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$  (Per Leg)

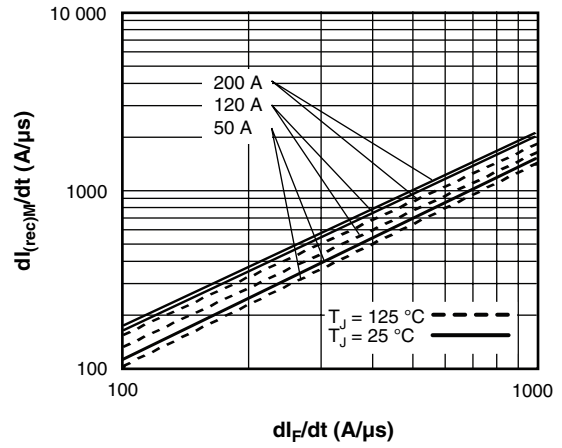


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$  (Per Leg)

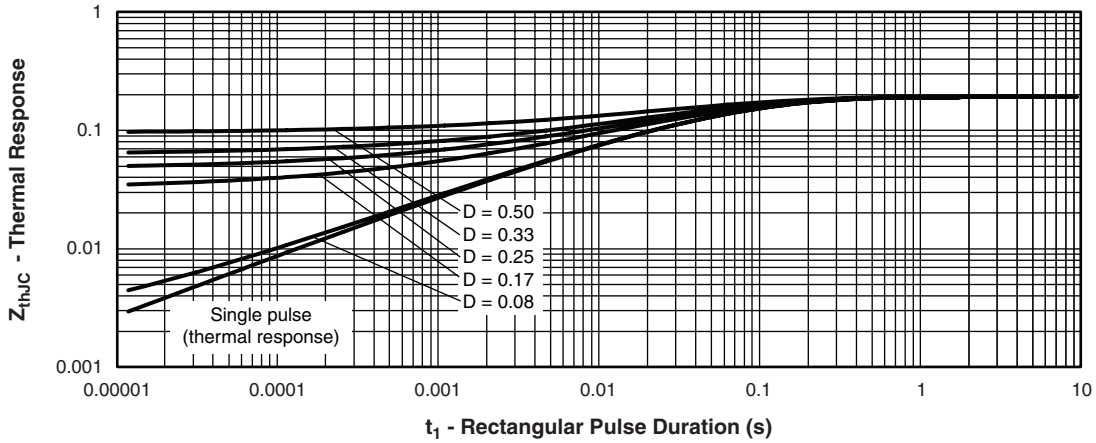


Fig. 9 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (Per Leg)

## HEXFRED® Ultrafast Soft Recovery Diode, 240 A

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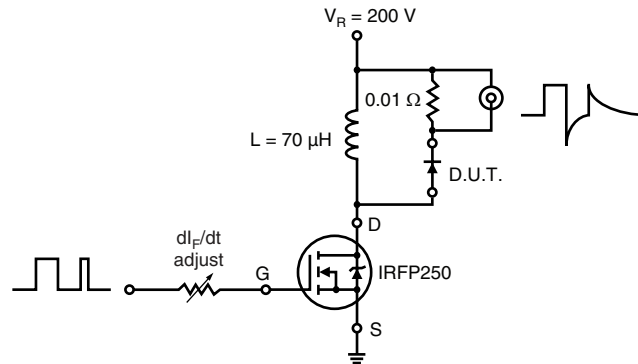
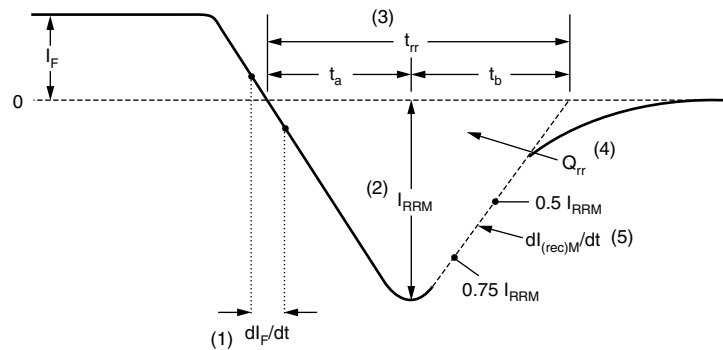


Fig. 10 - Reverse Recovery Parameter Test Circuit



(1)  $di_F/dt$  - rate of change of current through zero crossing

(2)  $I_{RRM}$  - peak reverse recovery current

(3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.

(4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 11 - Reverse Recovery Waveform and Definitions

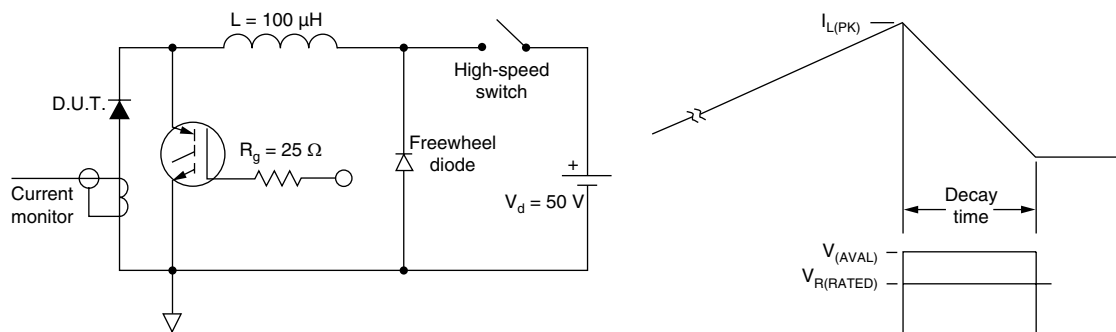


Fig. 12 - Avalanche Test Circuit and Waveforms

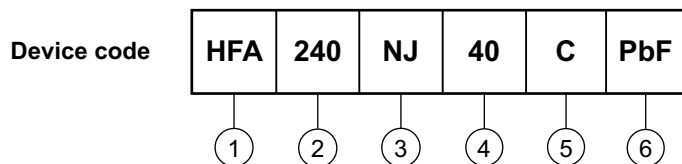
# HFA240NJ40CPbF

Vishay High Power Products

HEXFRED®  
Ultrafast Soft Recovery  
Diode, 240 A



## ORDERING INFORMATION TABLE



- 1** - HEXFRED® family, electron irradiated
- 2** - Average current rating
- 3** - NJ = TO-244
- 4** - Voltage rating (400 V)
- 5** - C = Common cathode
- 6** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95021">http://www.vishay.com/doc?95021</a>



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